Low Temperature Neutron Diraction Study of MnTe

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A bstract

Investigation of transport and magnetic properties of MnTe at low temperatures showed anomalies like negative coecient of resistance below 100K and a sharp rise in susceptibility at around 83K similar to a ferrom agnetic transition. Low temperature powder neutron direction experiments were therefore carried out to understand the underlying phenomena responsible for such anomalous behavior. Our study indicates that the rise in susceptibility at low temperatures is due to strengthening of ferromagnetic interaction within the plane over the interplane antiferromagnetic interactions.

K ey words: Neutron di raction; M nTe; M agnetic Sem iconductor; M agnetic Structure; A ntiferrom agnet

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1 Introduction

Compounds of 3d transition metals with VIB elements have a good combination of both electrical and magnetic properties. Because of their interrelation

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and incomplete d-shell of the component transition metals, they exhibit a variety of structural, m agnetic, electrical, optical and therm alproperties. As a consequence of this diversity they have excited considerable interest. They generally crystallize in the hexagonal N iAs type structure although a few of them possess cubic N aCl type structure. These N iAs type structures are important because of the interesting magnetic as well as electrical properties arising from the incomplete d shells of the component transition metals [1] and are of great interest both from experim ental and theoretical point of view [2,3]. Besides transform ation between magnetic phases, in some cases the transitions accompany a change in crystal structure. Special attention is devoted to the anomalies of magnetic, elastic and electrical properties of these substances which arise at the phase transition and the nature of which has not yet been understood. In particular all these anom alies have been observed in com pounds containing manganese viz., M nAs, M nSb, M nTe etc. [4]. M anganese chalcogenides, M nS, M nSe and M nTe are antiferrom agnetic com pounds with transition temperatures increasing with molecular weight [5,6]. In the case of M nS and M nSe the stable crystal structure is cubic N aCl type and these are wide gap insulators. [7,8,9]. On the other hand MnTe crystallizes in the hexagonal N iAs type structure [10] and it is one of the few sem iconductors am ong the 3d transition metal compounds. MnTe has electrical and magnetic properties sim ilar to those of NaCl type chalcogenide magnetic insulators but has a crystal structure which normally supports metallic conductivity. It is a p-type sem iconductor with a direct band gap of about 1.3 eV. It orders antiferrom agnetically at N eel tem perature, T_N 310K [11,12,13,14]. Changes in the tem perature dependence of resistivity near T_N have been attributed to spin disorder scattering i.e. scattering by magnons [15], a behaviour normally seen in ferrom agnetic m aterials [16]. The anomalies near the $T_{\rm N}$ in the therm oelectric power [17] and the Halle ect [18] are all related to the interaction of the charge carriers with the localized spins i.e. magnon drag e ect [15], a phenom enon sim ilar to phonon drag in non magnetic sem iconductors. MnTe behaves like an ionic crystal since the tellurium states prevail in the valence band, while the manganese states prevail in the conduction band. On the other hand dispersion of the bands indicate strong covalent e ects. Thus M nTe is a crossroad m aterial sharing properties of both broad band sem iconductors and ionic salts [7].

In this paper we report the results of the study of crystal and m agnetic structure of M nTe at low tem peratures. The transport and m agnetic m easurements such as resistivity and D $\mathcal L$. susceptibility carried out on polycrystalline M nTe showed anom alous behaviour at low tem peratures. A rise in resistivity below 100K accompanied by a rise in D $\mathcal L$. susceptibility at around the same temperature (83K), indicative of a ferrom agnetic like transition was observed. Neutron direction studies in the temperature range 10K to 300K were carried out to understand these anomalies and to elucidate the low temperature crystal and magnetic structure of this compound.

2 Experim ental

Polycrystalline sam ples of M nTe were prepared by the standard solid state route. The stoichiom etric amount of the starting materials, M n and Te in metallic form were ground, pelletized and vacuum sealed in an quartz ampoule below 10^6 Torr which was then annealed at a temperature of 750 C for 10 days. The sam ple formed was single phase and hom ogeneous with N iAs structure as con med by X-ray direction. The lattice parameter values calculated from the X-ray direction pattern were a = 4.190 0.001 A and c = 6.751 0.001 A.

The sam ple was then characterized by tem perature dependent resistivity measurem entusing the standard four probe technique. The DC susceptibility measurem ent was performed on the Faraday balance. In order to understand the nature of the anomalies seen in resistivity and susceptibility of MnTe neutron diraction study has been performed on this sample. Neutron diraction experiments were carried out in the temperature range 10K to 300K at the wavelength of 1242 A using the Prole Analysis Diractometer at Dhruva reactor, Trombay.

3 Results and Discussion

The resistivity and D .C . susceptibility as a function of tem perature for M nTe is shown in gure 1. M nTe is a sem iconductor at room tem perature and the resistivity is expected to increase with decreasing tem perature. However, the positive coe cient of resistivity seen below the magnetic ordering tem perature $T_{\rm N}=310{\rm K}$ is due to the spin disorder scattering with a large contribution from the in uence of magnon drag [16]. As the tem perature is further lowered, a rise in resistivity is observed below 100 K . The D C . susceptibility exhibits a sudden drop at 310 K indicating an antiferrom agnetic order in agreement to the earlier reports. The anomaly observed here is the sharp rise in susceptibility around 83 K suggestive of a ferrom agnetic like order.

In order to understand the origin of these anom alous behaviour at low tem – perature, powder neutron di raction measurements on MnTe as a function of tem perature were carried out. Pro le re nement of the mentioned di raction data at various tem peratures was carried out using the FULLPROF program [19]. The 300K pattern recorded for the entire setting of the detector i.e. from 2 = 8 to 96 is shown in gure 2. An intense Bragg peak due to the antiferrom agnetic ordering of Mn sub-lattice is seen at 2 = 10 in the 300K pattern along with the peaks corresponding to the NiAs type chemical structure. This pattern shows MnTe to be hexagonal with lattice parameters a =

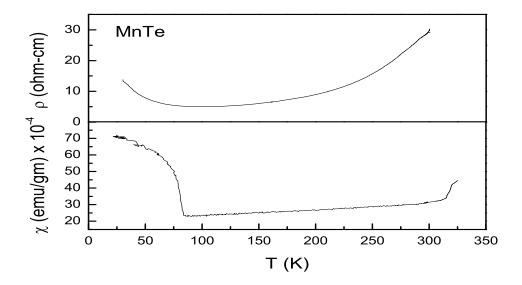


Fig. 1. Resistivity and Susceptibility of MnTe as a function of temperature

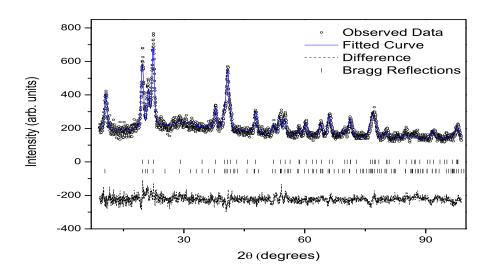


Fig. 2. Neutron Di raction Pattern of MnTe at 300K. The top set of vertical lines refer to nuclear Bragg re ections whereas the bottom set indicate positions of magnetic Bragg re ections.

4.193~0.001A, c=6.752~0.001A, in close agreement to those obtained from X-ray direction pattern [not shown]. The structural parameters obtained from Rietveld renement of the room temperature pattern are presented in Table 1. Since the magnetic form factor for neutrons falls drastically at higher angles, the low temperature direction data are limited upto 2=35 and are presented in the gure 3. The patterns could be tted well with two phase renement of nuclear and magnetic phases of MnTe. The magnetic cell of MnTe

could be viewed as M n m om ents aligned ferrom agnetically in the basal plane and these planes stacked antiferrom agnetically along the c-axis which is in agreem ent with those reported in literature [14,20]. The magnetic moment per M n ion is found to be 0.92 $_{\rm B}$ at 300K . The parameters obtained at room temperature were used as inputs to rene the neutron direction data at lower temperatures. The parameters rened were cell parameters and magnetic moment parameters, M $_{\rm X}$ and M $_{\rm Y}$. The tted patterns to the experimental data at dierent temperatures are shown in gure 3 as solid lines. A bænce of any extra peaks in the low temperature neutron direction patterns clearly rule out the possibility of any structural transition.

Table 1 Position coordinates, Isotropic temperature factor (B $_{\rm iso}$), 0 ccupancy/formula unit (0 cc./f.u.) and R-factors of R ietveld renement of 300K neutron diaction pattern of M nTe.

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A tom	Х	У	Z	$B_{iso}(A^2)$	0 cc./f.u.
Мn	0	0	0	0.84(1)	1.00(1)
Te	1/3	2/3	1/4	0.57(1)	0.98(1)

$$R_p = 5.8 \quad R_{wp} = 7.33 \quad R_{exp} = 6.48$$

Bragg R = 14.7 Magnetic R = 10.8

The number in the bracket represents uncertainty in the last digit.

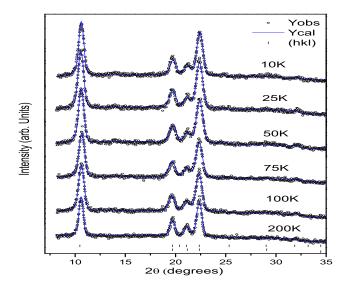


Fig. 3. Neutron Di raction pattern of MnTe at various temperatures. The top set of vertical lines refer to nuclear Bragg reections whereas the bottom set indicate positions of magnetic Bragg reections.

A plot of magnetic moment per M n ion estimated from our analysis is shown

in gure 4. It is seen that the magnetic moment decreases from $2.06_{\rm B}$ at $10{\rm K}$ to $0.92_{\rm B}$ at $300{\rm K}$. The variation of magnetic moment with temperature shows the Brillouin function type of dependence. The expected value of the ordered moment at T = 0 K is $5_{\rm B}$. Instead, a reduced moment of $2_{\rm B}$ is observed. This is perhaps due to large dispersion of M n bands in M nTe which results in M n 3d band being more than half-lled. The rise in susceptibility below 83K could be due to a tilt in magnetic moment away from the basal plane. However, a tilt in magnetic moment vector away from the basal plane would have resulted in increase in intesity of magnetic f102g rejection (at 2=22.35) and decrease in the intensity of magnetic f102g rejection (at 2=10.46). In the present case, the intensity of magnetic f102g rejection as a function of temperature, exactly follows the intensity of magnetic f002g rejection. This leads us to be lieve that there is no tilt in the magnetic moment vector away from the basal plane. Therefore other possibilities have to be considered to explain the increase of susceptibility below 83K.

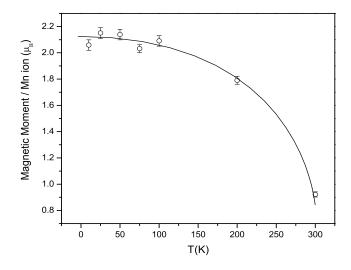


Fig. 4. Variation of M agnetic M om ent with temperature. Solid line is just a line through the points

Owing to the magnetic stucture of MnTe, the magnetic interactions seem to be strongly associated with the structural parameters and any change in the latter would a ect the overall magnetic interactions. In the present study, as can be seen in gure 5, a and c and therefore the c=a ratio remain constant upto around 200K. The c=a then decreases upto 75K with c and a having a minimum and maximum values respectively. Below 75K c=a ratio increases sharply with decreasing temperature due to an increase in c and decrease in a values. The Mn-Mn interatom ic distance in the basal plane is equal to a while along the perpendicular axis it is given by c=2. It can be clearly seen from gure 5 the change in c below 75K is much smaller than the corresponding

change in a. Therefore the decrease in a would strengthen the ferrom agnetic interactions between the M n ions in the basal plane at the same time the increase in cweakens the antiferrom agnetic interactions. Such a weakening of interplanar coupling can also explain the small rise seen in resistivity at low temperatures. It may be noted that no ferrom agnetic signature is detected in neutron direction patterns below 75 K that could be attributed to any structural transition. Hence the observed anomalies below 100K in the resistivity and susceptibility measurements are due to a magneto-elastic coupling wherein the M n ions are slightly displaced without producing any drastic change in the overall crystal structure.

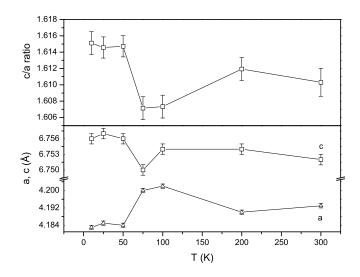


Fig. 5. Variation of lattice parameters and the c/a ratio with temperature.

4 Conclusion

The resistivity and susceptibility measurements as a function of temperature for MnTe were carried out. The uptum in the susceptibility at around 83K hinted towards some kind of structural transition. However, a detailed analysis of the powder neutron direction measurements in the temperature range 10K to 300K do not show any evidence of an extra phase to be present within the limited statistics of the data. The rise in susceptibility below 83K could be explained to be due to a magneto-elastic coupling which strengthens intraplanar ferromagnetic interactions relative to interplanar antiferromagnetic interactions.

A cknow ledgm ents

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